

Docket No. 24061.188 (TSMC2003-1374)  
Customer No. 42717

FJW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:	Chun-Chieh Lin	§ Docket No.: 24061.188 (TSMC2003-1374)
Serial No.:	10/816,730	§ Examiner: To Be Determined
Filing Date:	April 2, 2004	§ Art Unit: 2818
Entitled:	MRAM Device Having Low-K Inter-Metal Dielectric	§ Conf. No.: 1025 §

INFORMATION DISCLOSURE STATEMENT

Commissioner For Patents  
P.O. Box 1450, M/S Amendments  
Alexandria, VA 22313-1450

Dear Sir:

In compliance with the duty of disclosure under 37 CFR §1.56, and in accordance with the practice under 37 CFR §1.97 and §1.98, the Examiner's attention is directed to the documents listed on the enclosed modified Form PTO-1449. No inference should be made that the cited references are in fact material, are in fact prior art, or that no better art exists. The cited patents are listed in numerical order and are not in any order based on their pertinence.

The above-identified application was filed after June 30, 2003. Therefore, pursuant to the waiver of the requirement under 37 CFR 1.98 (a)(2)(i) as stated in a Pre-OG Notice dated July 11, 2003, copies of the U.S. patents listed on the enclosed modified Form PTO-1449 are not being provided.

This Information Disclosure Statement is being filed within three months of the United States filing date or before the mailing date of a first Office Action on the merits. No certification or fee is required (37 CFR §1.97(b)).

It is respectfully requested that the above information be considered by the Examiner and that a copy of the enclosed Form PTO-1449 be returned indicating that such information has been considered.

Respectfully submitted,

Dave R. Hofman  
Registration No. 55,272

Date: 9/7/04

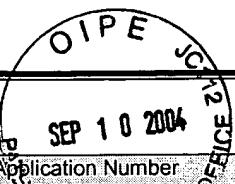
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Certificate of Mailing

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to Commissioner For Patents, P.O. Box 1450, M/S Amendment, Alexandria, VA 22313-1450 on the date indicated below.

Bonnie Boyle  
Name

9-7-04

In place of PTO-1449 Form	U. S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			Complete if Known
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>				 <b>SEP 10 2004</b> <small>SEARCHED INDEXED MAILED</small>
SHEET	1	OF	1	
				Attorney Docket Number
				24061.188 (TSMC2003-1374)

#### U. S. PATENT DOCUMENTS

Examiner's Initials	Cite No.	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
	AA	5956267	09-21-1999	Hurst, et al.
	AB	6005800	12-21-1999	Koch, et al.
	AC	6114719	09-05-2000	Dill, et al.
	AD	6335890	01-01-2002	Reohr, et al.
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	AJ	6509621	01-21-2003	Nakao
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	AU	6693822	02-17-2004	Ito
	AV	6693826	02-18-2004	Black, Jr., et al.
	AW	2002/0105827 A1	08-08-2002	Redon, et al.
	AX	2003/0048676 A1	03-13-2003	Daughton, et al.
	AY	2003/0086313 A1	05-08-2003	Asao
	AZ			

#### FOREIGN PATENT DOCUMENTS

Examiner's Initials	Cite No.	Foreign Patent Document (Country Code – Number – Kind)	Publication Date MM-DD-YYYY	Patentee or Applicant of Cited Document	Translation Y/N

#### OTHER PRIOR ART

Examiner's Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article, title of the item, date, page(s), volume-issue number(s), publisher, city/country where published
	BA	SAITO, YOSHIaki, ET AL., "Correlation Between Barrier Width, Barrier Height, and DC Bias Voltage Dependencies on the Magnetoresistance Ratio in Ir-Mn Exchange Biased Single and Double Tunnel Junctions", The Japan Society of Applied Physics, Vol. 39, 2000, pp. L1035-L1038.
	BB	MONTAIGNE, F., ET AL., "Enhanced Tunnel Magnetoresistance at High Bias Voltage in Double-Barrier Planar Junctions", Applied Physics Letters, Vol. 73, No. 19, November 9, 1998, pp. 2829-2831.
	BC	ANGUELOUCH, A., "Two-Dimensional Magnetic Switching of Micron-Size Films in Magnetic Tunnel Junctions", Applied Physics Letters, Vol. 76, No. 5, January 31, 2000, pp. 622-624.

Examiner Signature		Date Considered	
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include a copy of this form with next communication to applicant.